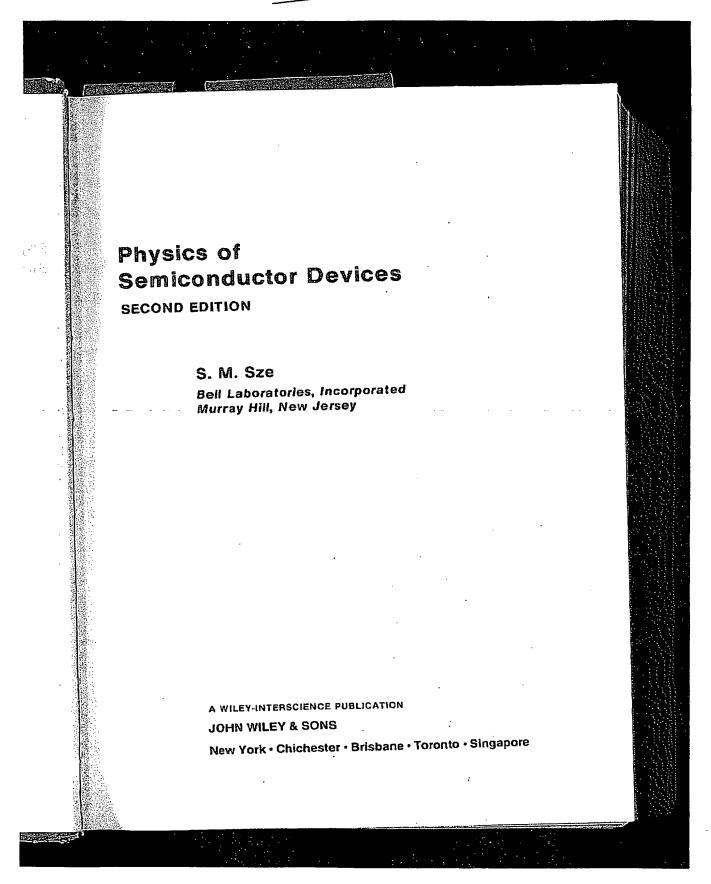
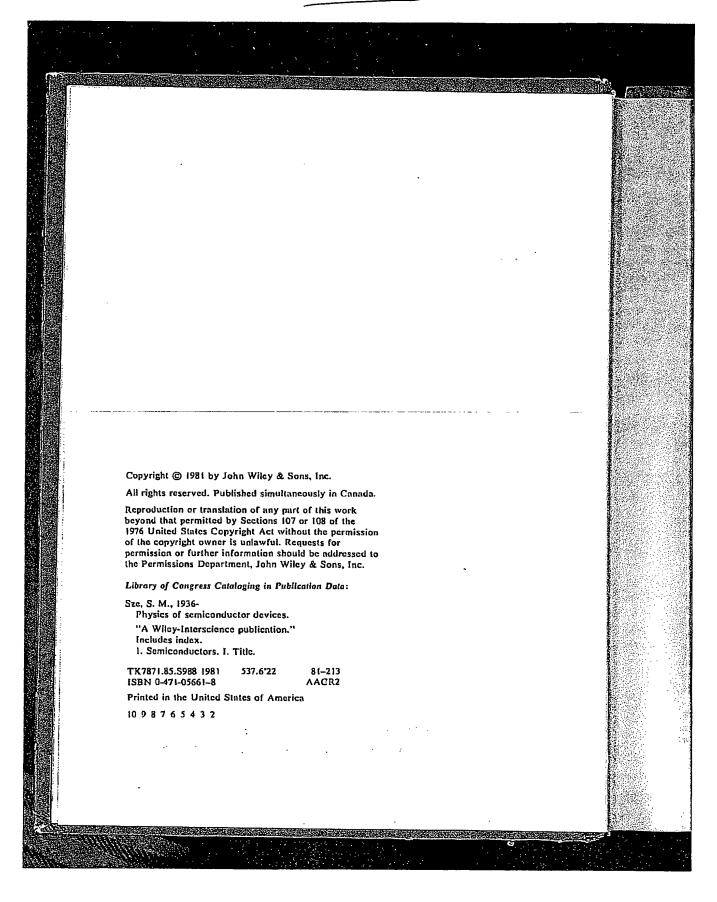
## EXHIBIT 1 FOLLOWS THIS DIVIDER PAGE

Exhibit 1





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Appendix I			
Properties of SiO <sub>2</sub>		<b>∂</b> ;	
and Si <sub>3</sub> N <sub>4</sub> at 300 K			
and Sign4 at 500 R		· ·,	
Insulator:	SiO <sub>2</sub>	Si <sub>3</sub> N <sub>4</sub>	
Structure	Amorphous	Amorphous	- 1
Melting point (°C)	~1600	***	14.7
Density (g/cm³)	2,2	3.1	
Refractive index	1.46	2.05	•
Dielectric constant	3.9	7.5	
Dielectric strength (V/cm)	107	107	
Infrared absorption band (µm)	9.3	11.5-12.0	٠
Energy gap (eV)	9	~5.0	
Thermal-expansion coefficient (°C <sup>-1</sup> )	5×10 <sup>-7</sup>	<del></del> -	•
Thermal conductivity (W/cm-K)	0.014		
dc resistivity (Ω-cm)	10 <sup>14</sup> 10 <sup>16</sup>	~1014	
at 25°C at 500°C	1010	~10 <sup>13</sup>	
Etch rate in buffered HF	1000	5-10	
(Å/min)		, - 10	• •
Buffered HF: 34.6% (wt.) NH <sub>4</sub> F, 6.8% (wt.)	) HF, 58.6% H <sub>2</sub> 0	ο.	
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•			
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## EXHIBIT 2 FOLLOWS THIS DIVIDER PAGE